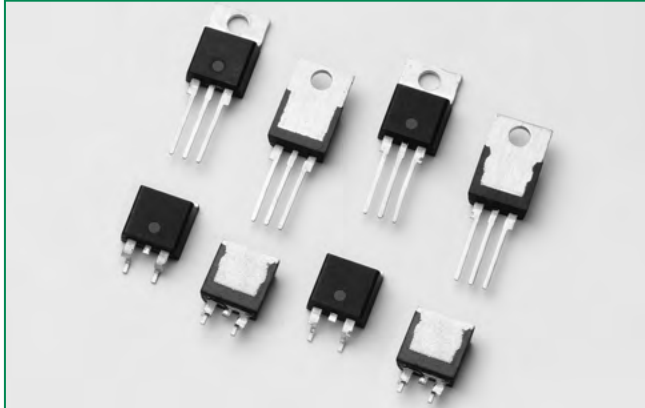



# SJxx32xxA Series



Note: xx = voltage/10, x=package

## Agency Recognitions

Agency	Agency File Number
	E71639

Note: L package only

## Main Features

Symbol	Value	Unit
$I_{T(RMS)}$	32	A
$V_{DRM}/V_{RRM}$	400 or 600	V
$I_{GT}$	15 or 40	mA

## Description

This SJxx32xxA high temperature SCR series is ideal for uni-directional switch applications such as phase control in heating, motor speed controls and AC rectifier and voltage regulator.

This SCR series offer low gate current trigger levels of 15 mA or 40 mA at approximately 1.5V.

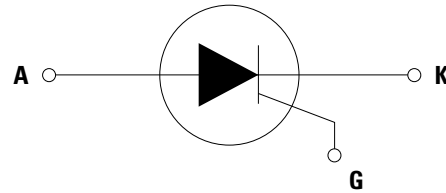
## Features & Benefits

- High junction temperature
- Voltage capability up to 600 V
- Surge capability up to 380 A at 60 Hz half cycle
- AEC-Q101 qualified
- Recognized to UL 1557 as an Electrically Isolated Semiconductor Device
- Halogen-free and ROHS compliant

## Applications

Typical applications are AC rectifier, voltage regulator, AC solid-state switches, industrial power tools, exercise equipment, white goods and commercial appliances.

## Schematic Symbol



## Absolute Maximum Ratings

Symbol	Parameter	Test Conditions	Value	Unit
$V_{DSM}/V_{RSM}$	Peak non-repetitive blocking voltage	$P_w = 100\mu s$	700	V
$I_{T(RMS)}$	RMS on-state current	SJxx32LxA $T_c = 80^\circ C$	32	A
		SJxx32RxA/SJxx32NxA $T_c = 115^\circ C$		
$I_{T(AV)}$	Average on-state current	SJxx32LxA $T_c = 80^\circ C$	20	A
		SJxx32RxA/SJxx32NxA $T_c = 115^\circ C$		
$I_{TSM}$	Peak non-repetitive surge current	single half cycle; $f = 50Hz$ ; $T_J$ (initial) = $25^\circ C$	320	A
		single half cycle; $f = 60Hz$ ; $T_J$ (initial) = $25^\circ C$	380	
$I^2t$	$I^2t$ Value for fusing	$t_p = 8.3 ms$	640	$A^2s$
$di/dt$	Critical rate of rise of on-state current	$f = 60Hz$ ; $T_J = 150^\circ C$	150	$A/\mu s$
$I_{GM}$	Peak gate current	$t_p \leq 10\mu s$ ; $T_J = 150^\circ C$	4	A
$P_{G(AV)}$	Average gate power dissipation	$t_p \leq 10\mu s$ ; $T_J = 150^\circ C$	1	W
$T_{stg}$	Storage temperature range		-40 to 150	$^\circ C$
$T_J$	Operating junction temperature range		-40 to 150	$^\circ C$

### Electrical Characteristics ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)

Symbol	Test Conditions		SJxx32xA	SJxx32x2A	Unit	
$I_{GT}$	$V_D = 12\text{V}; R_L = 30\ \Omega$	MAX.	40	15	mA	
		MIN.	5	3		
$V_{GT}$		MAX.	1.5		V	
dv/dt	$V_D = V_{DRM}; \text{gate open}; T_J = 125^\circ\text{C}$	400V	MIN.	650	400	V/ $\mu\text{s}$
		600V		600	350	
	$V_D = V_{DRM}; \text{gate open}; T_J = 150^\circ\text{C}$	400V		550	-	
		600V		500	-	
	$V_D = 67\%V_{DRM}; \text{gate open}; T_J = 150^\circ\text{C}$	400V		-	300	
		600V		-	250	
$V_{GD}$	$V_D = V_{DRM}; R_L = 3.3\ \text{k}\Omega; T_J = 150^\circ\text{C}$	MIN.	0.2		V	
$I_H$	$I_T = 400\text{mA}$ (initial)	MAX.	60	50	mA	
$t_q$	$I_T = 2\text{A}; t_p = 50\ \mu\text{s}; dv/dt = 5\text{V}/\mu\text{s}; di/dt = -30\text{A}/\mu\text{s}$	MAX.	35		$\mu\text{s}$	
$t_{gt}$	$I_G = 2 \times I_{GT}; \text{PW} = 15\ \mu\text{s}; I_T = 64\text{A}$	TYP.	2		$\mu\text{s}$	

Note: xx = voltage/10, x=package

### Static Characteristics

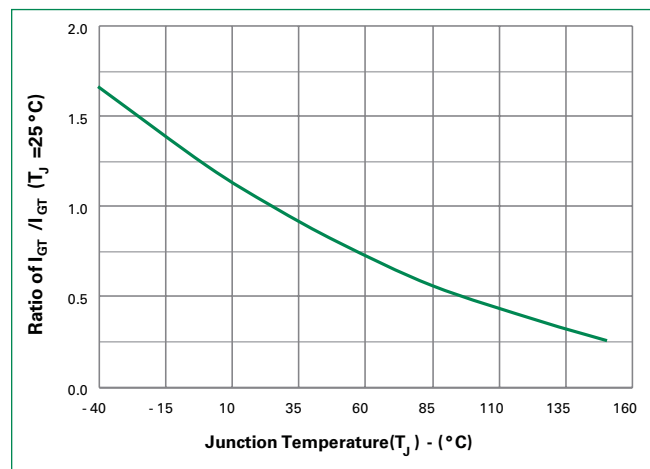
Symbol	Test Conditions		Value	Unit	
$V_{TM}$	$I_T = 64\text{A}; t_p = 380\ \mu\text{s}$	MAX.	1.6	V	
$I_{DRM} / I_{RRM}$	@ $V_{DRM} / V_{RRM}$	$T_J = 25^\circ\text{C}$	MAX.	10	$\mu\text{A}$
		$T_J = 125^\circ\text{C}$		2000	
		$T_J = 150^\circ\text{C}$		4000	

### Thermal Resistances

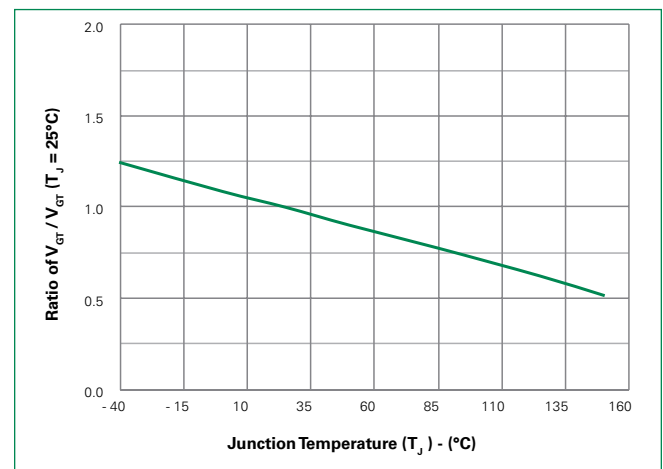
Symbol	Parameter	Value	Unit
$R_{\theta(UC)}$	SJxx32LxA	1.9	$^\circ\text{C}/\text{W}$
	SJxx32RxA/SJxx32NxA	0.8	

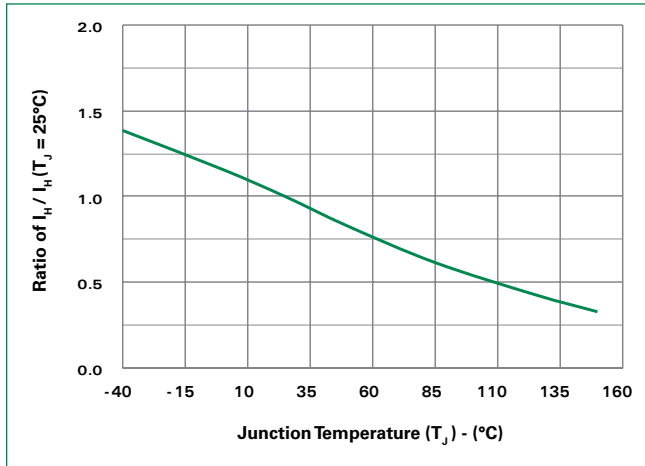
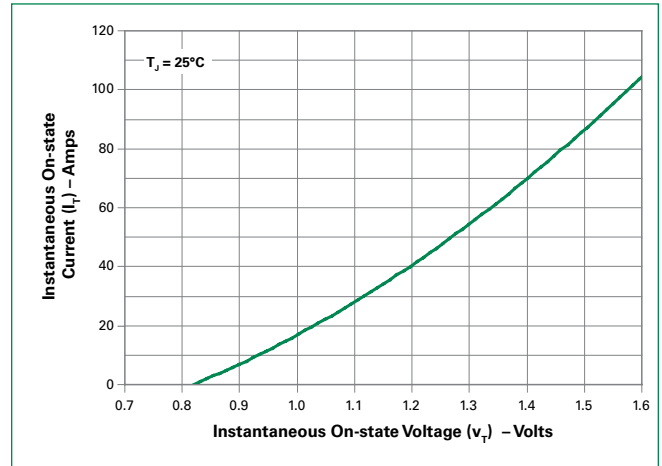
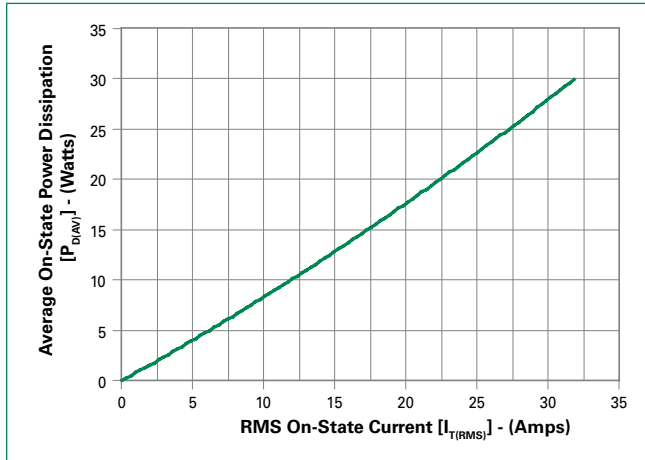
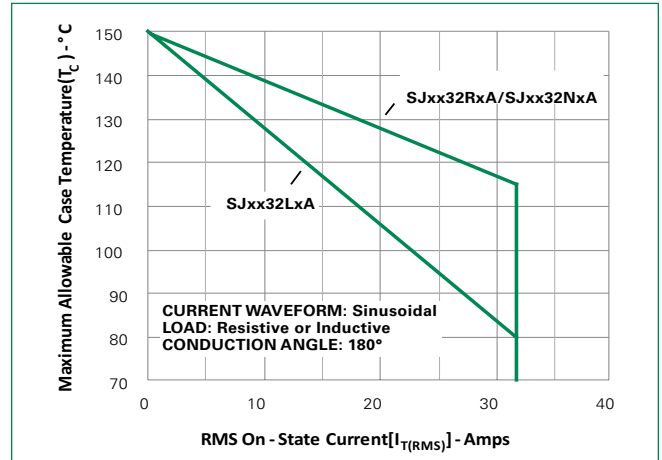
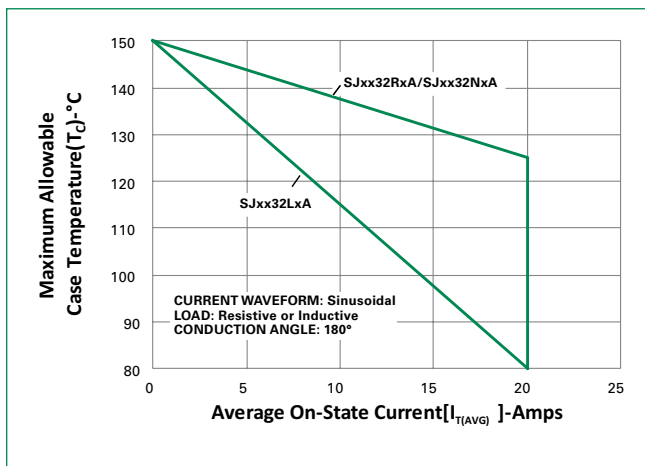
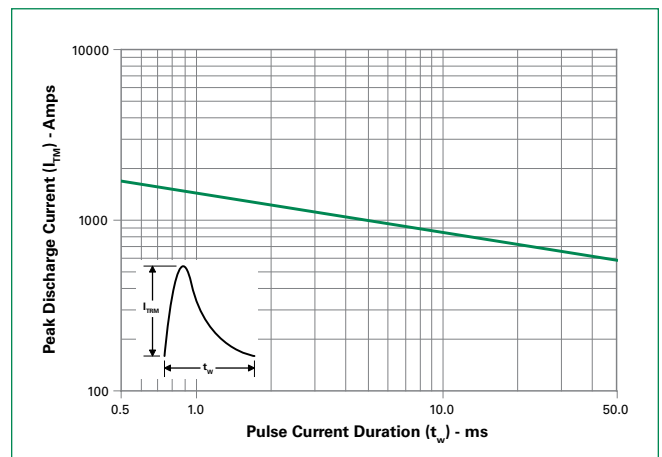
Note: xx = voltage, x = sensitivity & type

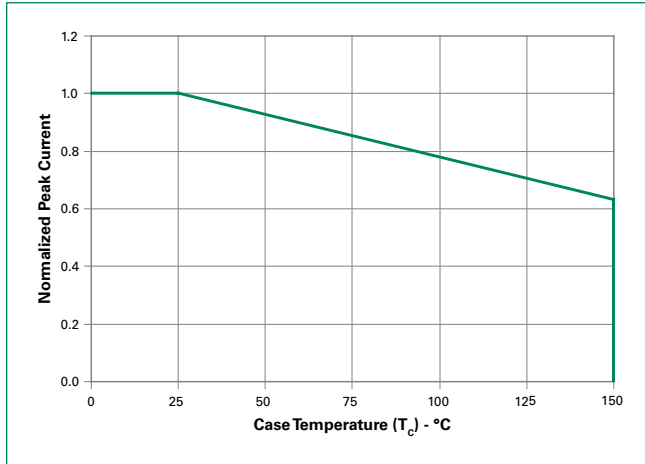
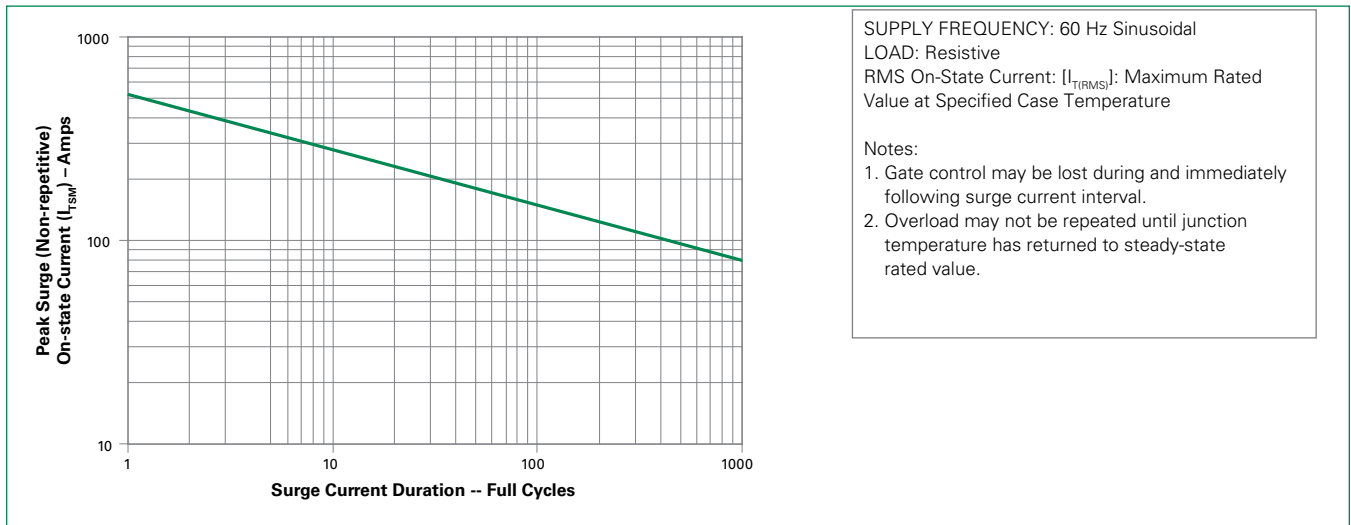
**Figure 1: Normalized DC Gate Trigger Current vs. Junction Temperature**



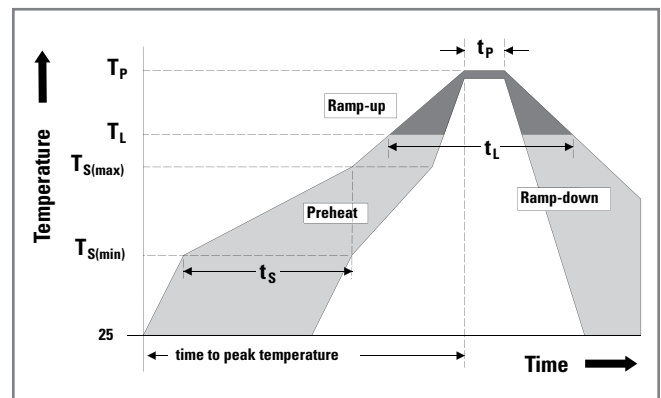
**Figure 2: Normalized DC Gate Trigger Voltage vs. Junction Temperature**



**Figure 3: Normalized DC Holding Current vs. Junction Temperature**

**Figure 4: On-State Current vs. On-State Voltage (Typical)**

**Figure 5: Power Dissipation (Typical) vs. RMS On-State Current**

**Figure 6: Maximum Allowable Case Temperature vs. RMS On-State Current**

**Figure 7: Maximum Allowable Case Temperature vs. Average On-State Current**

**Figure 8: Peak Capacitor Discharge Current**


**Figure 9: Peak Capacitor Discharge Current Derating**

**Figure 10: Surge Peak On-State Current vs. Number of Cycles**

**Soldering Parameters**

Reflow Condition	Pb – Free assembly	
Pre Heat	- Temperature Min ( $T_{s(min)}$ )	150°C
	- Temperature Max ( $T_{s(max)}$ )	200°C
	- Time (min to max) ( $t_s$ )	60 – 180 secs
Average ramp up rate (Liquidus Temp) ( $T_L$ ) to peak	5°C/second max	
$T_{s(max)}$ to $T_L$ - Ramp-up Rate	5°C/second max	
Reflow	- Temperature ( $T_L$ ) (Liquidus)	217°C
	- Time ( $t_l$ )	60 – 150 seconds
Peak Temperature ( $T_p$ )	260 <sup>+0/-5</sup> °C	
Time within 5°C of actual peak Temperature ( $t_p$ )	20 – 40 seconds	
Ramp-down Rate	5°C/second max	
Time 25°C to peak Temperature ( $T_p$ )	8 minutes Max.	
Do not exceed	280°C	



### Physical Specifications

<b>Terminal Finish</b>	100% Matte Tin-plated
<b>Body Material</b>	UL Recognized compound meeting flammability rating V-0
<b>Lead Material</b>	Copper Alloy

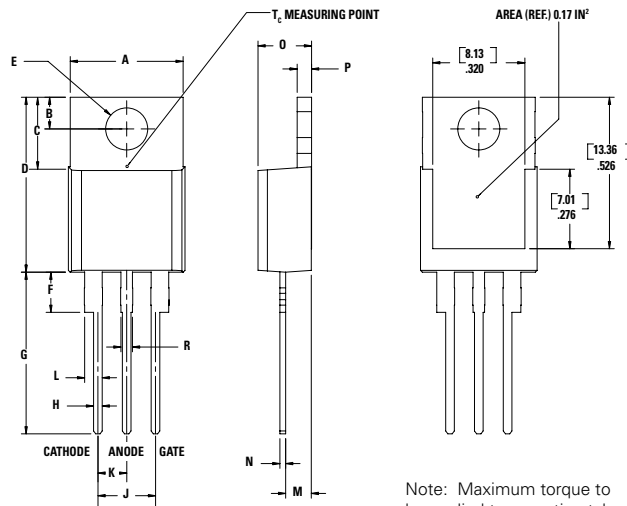
### Design Considerations

Careful selection of the correct component for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the component rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including  $dv/dt$ ), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

### Environmental Specifications

Test	Specifications and Conditions
<b>AC Blocking</b>	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 150°C for 1008 hours
<b>Temperature Cycling</b>	MIL-STD-750, M-1051, 1000 cycles; -55°C to +150°C; 15-min dwell-time
<b>Temperature/Humidity</b>	EIA / JEDEC, JESD22-A101 1008 hours; 160V - DC: 85°C; 85% rel humidity
<b>Resistance to Solder Heat</b>	MIL-STD-750 Method 2031
<b>Solderability</b>	ANSI/J-STD-002, category 3, Test A
<b>Lead Bend</b>	MIL-STD-750, M-2036 Cond E
<b>Moisture Sensitivity Level</b>	Level 1, JEDEC-J-STD-020D
<b>UHASt</b>	JESD22A-118,96hrs, 130oC/85%RH
<b>IOL</b>	MIL-STD-750 Method 1037

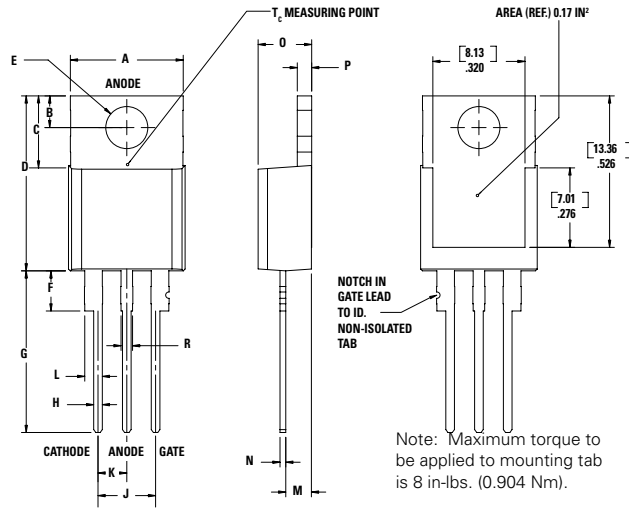
### Dimensions — TO-220AB (L-Package) — Isolated Mounting Tab



Note: Maximum torque to be applied to mounting tab is 8 in-lbs. (0.904 Nm).

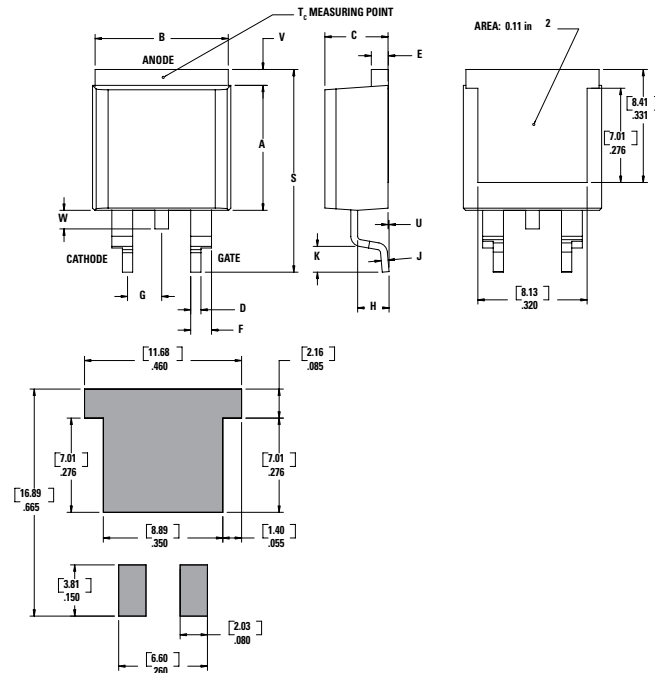
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

### Dimensions – TO-220AB (R-Package) – Non-Isolated Mounting Tab Common with Center Lead



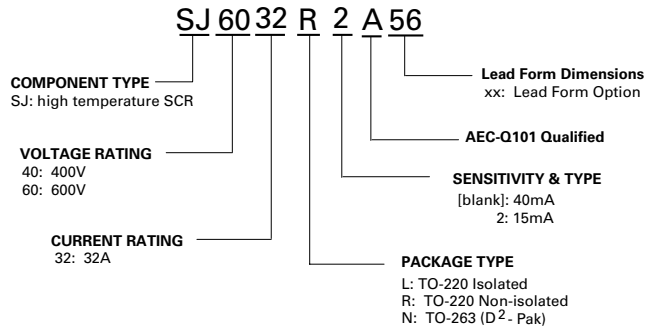
Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

### Dimensions – TO-263 (N-package) – D<sup>2</sup>-Pak Surface Mount

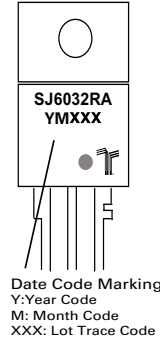


Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.360	0.370	9.14	9.40
B	0.380	0.420	9.65	10.67
C	0.178	0.188	4.52	4.78
D	0.025	0.035	0.63	0.89
E	0.048	0.055	1.22	1.40
F	0.060	0.075	1.52	1.91
G	0.095	0.105	2.41	2.67
H	0.083	0.093	2.11	2.36
J	0.018	0.024	0.46	0.61
K	0.090	0.110	2.29	2.79
S	0.590	0.625	14.99	15.87
V	0.035	0.045	0.89	1.14
U	0.002	0.010	0.05	0.25
W	0.040	0.070	1.02	1.78

### Part Numbering System



### Part Marking System



### Product Selector

Part Number	Voltage		Gate Sensitivity	Type	Package
	400V	600V			
SJxx32LA	X	X	40mA	Standard SCR	TO-220L
SJxx32RA	X	X	40mA	Standard SCR	TO-220R
SJxx32NA	X	X	40mA	Standard SCR	TO-263
SJxx32L2A	X	X	15mA	Standard SCR	TO-220L
SJxx32R2A	X	X	15mA	Standard SCR	TO-220R
SJxx32N2A	X	X	15mA	Standard SCR	TO-263

Note: xx = Voltage/10

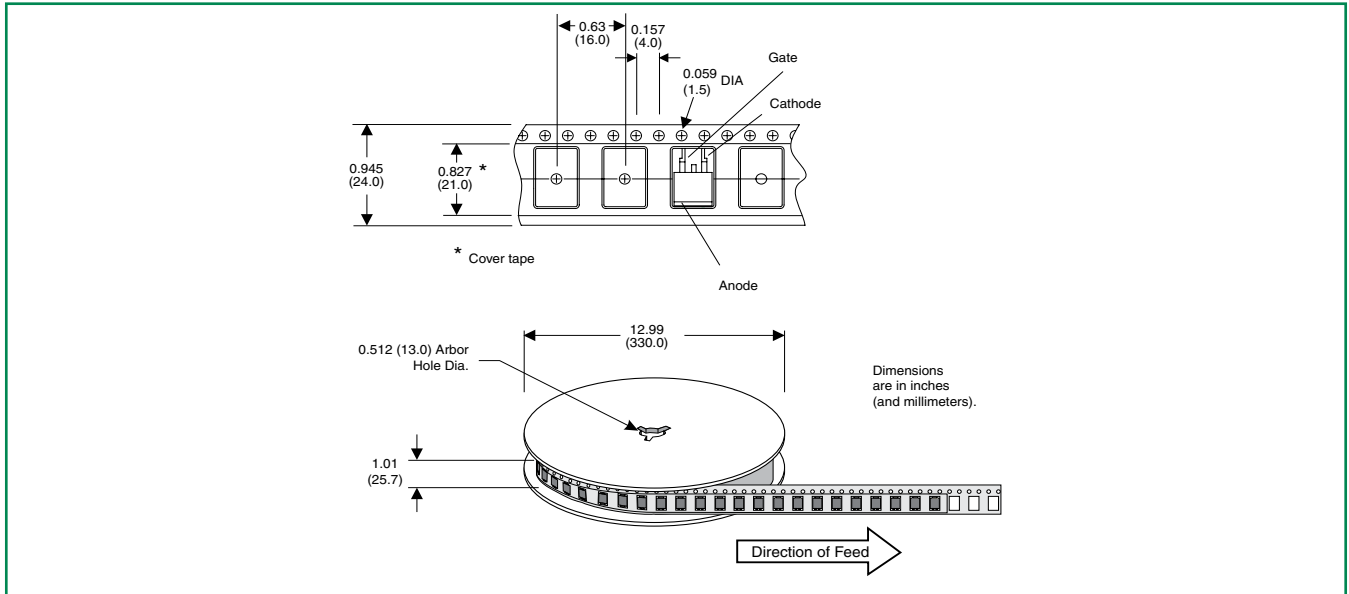
### Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
SJxx32LATP	SJxx32LA	2.2g	Tube	1000 (50 per tube)
SJxx32RATP	SJxx32RA	2.2g	Tube	1000 (50 per tube)
SJxx32NATP	SJxx32NA	1.6g	Tube	1000 (50 per tube)
SJxx32NARP	SJxx32NA	1.6g	Embossed Carrier	500
SJxx32L2ATP	SJxx32L2A	2.2g	Tube	1000 (50 per tube)
SJxx32R2ATP	SJxx32R2A	2.2g	Tube	1000 (50 per tube)
SJxx32N2ARP	SJxx32N2A	1.6g	Embossed Carrier	500
SJxx32N2ATP	SJxx32N2A	1.6g	Tube	1000 (50 per tube)

Note: xx = Voltage/10

### Reel Pack (RP) for TO-263 Embossed Carrier Specifications

Meets all EIA-481-2 Standards



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